



**QM300HA-24**

**HIGH POWER SWITCHING USE  
INSULATED TYPE**

**ABSOLUTE MAXIMUM RATINGS** (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	Ic=1A, VEB=2V	1200	V
VCEX	Collector-emitter voltage	VEB=2V	1200	V
VCBO	Collector-base voltage	Emitter open	1200	V
VEBO	Emitter-base voltage	Collector open	7	V
Ic	Collector current	DC	300	A
-Ic	Collector reverse current	DC (forward diode current)	300	A
PC	Collector dissipation	Tc=25°C	1980	W
Ib	Base current	DC	16	A
-IcSM	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	3000	A
Tj	Junction temperature		-40~+150	°C
Tstg	Storage temperature		-40~+125	°C
Viso	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Main terminal screw M6	1.96~2.94	N·m
			20~30	kg·cm
		Mounting screw M6	1.96~2.94	N·m
			20~30	kg·cm
		B terminal screw M4	0.98~1.47	N·m
			10~15	kg·cm
BX terminal screw M4	0.98~1.47	N·m		
	10~15	kg·cm		
—	Weight	Typical value	460	g

**ELECTRICAL CHARACTERISTICS** (Tj=25°C, unless otherwise noted)

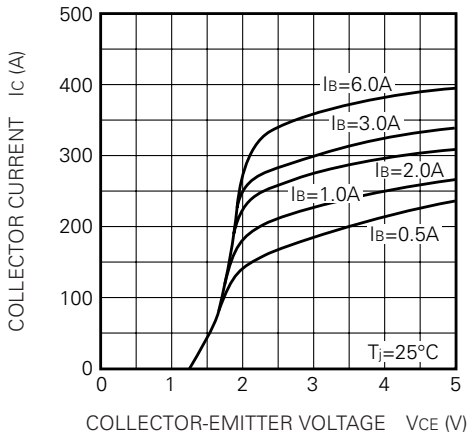
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IcEX	Collector cutoff current	VCE=1200V, VEB=2V	—	—	4.0	mA
IcBO	Collector cutoff current	VCB=1200V, Emitter open	—	—	4.0	mA
IeBO	Emitter cutoff current	VEB=7V	—	—	400	mA
VCE (sat)	Collector-emitter saturation voltage	Ic=300A, Ib=6A	—	—	3.0	V
VBE (sat)	Base-emitter saturation voltage	Ic=300A, Ib=6A	—	—	3.5	V
-VCEO	Collector-emitter reverse voltage	-Ic=300A (diode forward voltage)	—	—	1.8	V
hFE	DC current gain	Ic=300A, VCE=5V	75	—	—	—
ton	Switching time	VCC=600V, Ic=300A, Ib1=-Ib2=6A	—	—	3.0	μs
ts			—	—	15	μs
tf			—	—	3.0	μs
Rth (j-c) Q	Thermal resistance (junction to case)	Transistor part	—	—	0.063	°C/W
Rth (j-c) R		Diode part	—	—	0.3	°C/W
Rth (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied	—	—	0.04	°C/W

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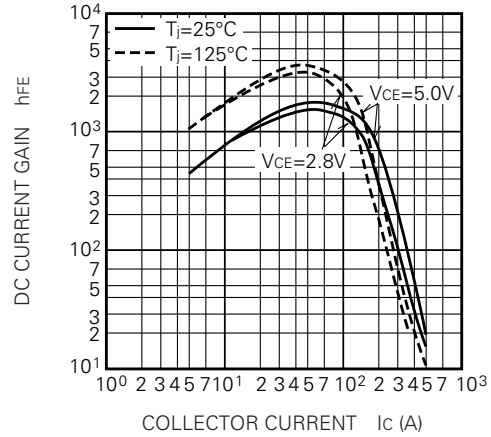
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

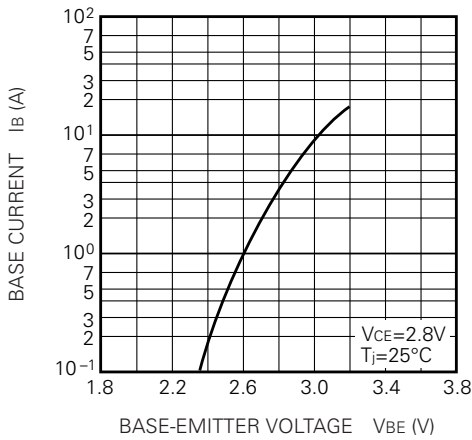
**COMMON EMITTER OUTPUT CHARACTERISTICS (TYPICAL)**



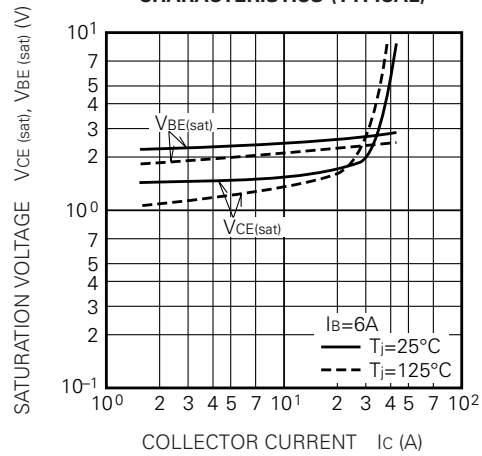
**DC CURRENT GAIN VS. COLLECTOR CURRENT (TYPICAL)**



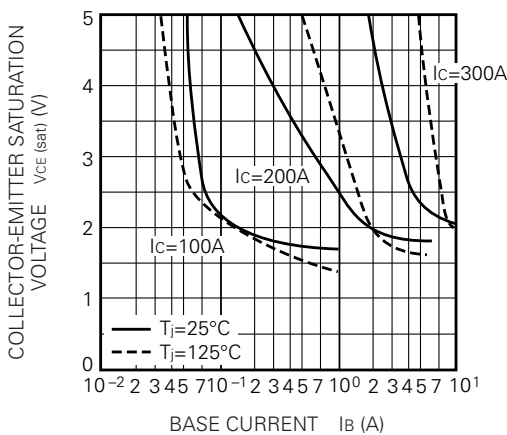
**COMMON EMITTER INPUT CHARACTERISTIC (TYPICAL)**



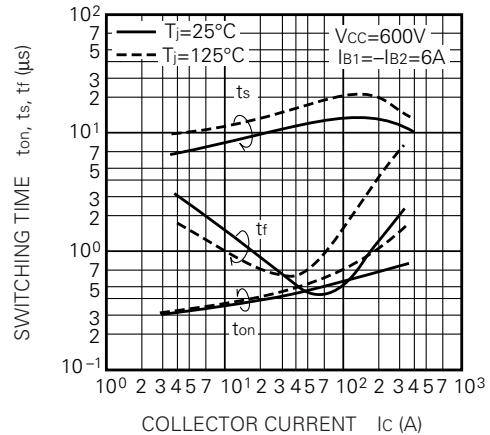
**SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



**COLLECTOR-EMITTER SATURATION VOLTAGE (TYPICAL)**



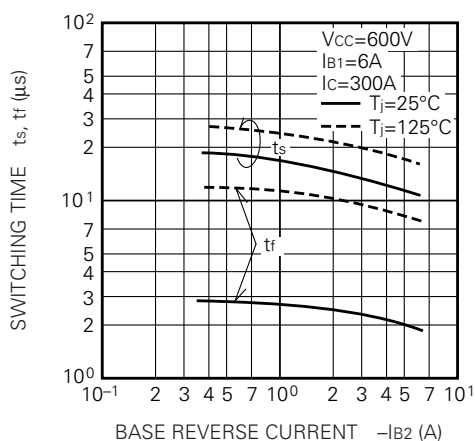
**SWITCHING TIME VS. COLLECTOR CURRENT (TYPICAL)**



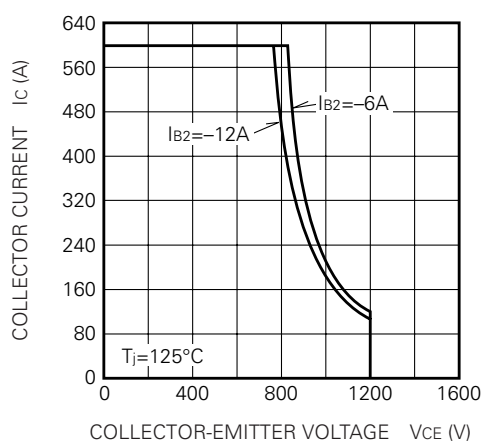
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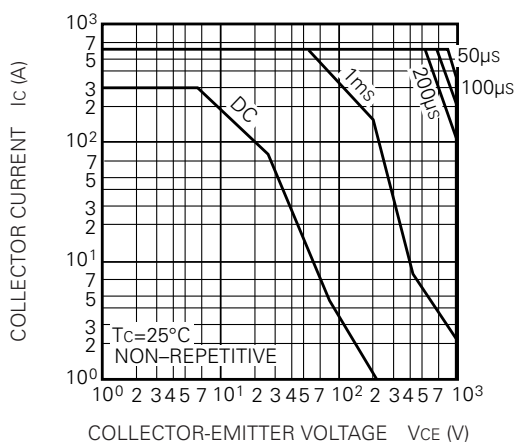
**SWITCHING TIME VS. BASE CURRENT (TYPICAL)**



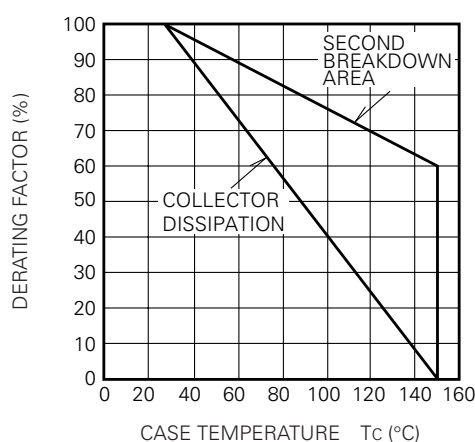
**REVERSE BIAS SAFE OPERATING AREA**



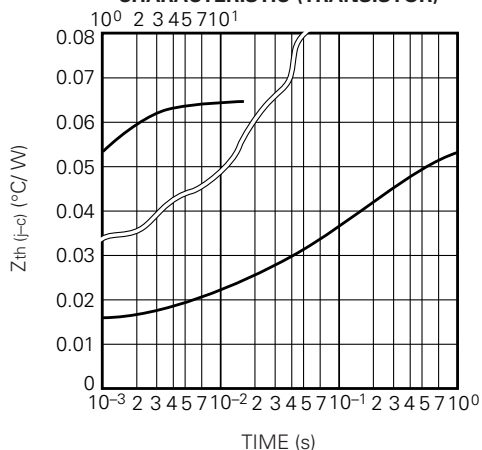
**FORWARD BIAS SAFE OPERATING AREA**



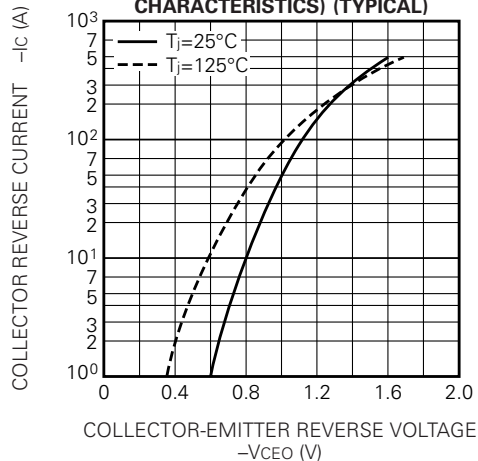
**DERATING FACTOR OF F. B. S. O. A.**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTIC (TRANSISTOR)**



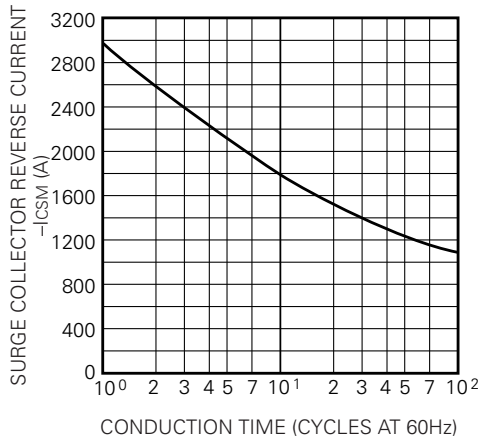
**REVERSE COLLECTOR CURRENT VS. COLLECTOR-EMITTER REVERSE VOLTAGE (DIODE FORWARD CHARACTERISTICS) (TYPICAL)**



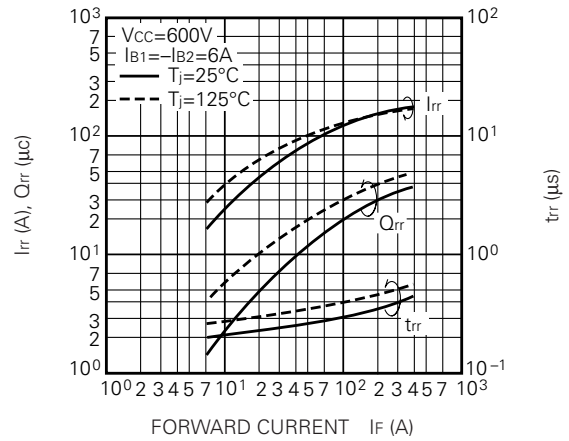
# QM300HA-24

HIGH POWER SWITCHING USE  
INSULATED TYPE

**RATED SURGE COLLECTOR REVERSE CURRENT  
(DIODE FORWARD SURGE CURRENT)**



**REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE  
CHARACTERISTIC (DIODE)**

